

PHASE CHANGEABLE MEMORY DEVICES HAVING REDUCED  
CELL AREAS AND METHODS OF FABRICATING THE SAME

ABSTRACT

5           Phase changeable memory devices include an integrated circuit substrate and first and  
second storage active regions on the integrated circuit substrate. The first and second storage  
active regions have a first width and a second width, respectively. A transistor active region  
on the integrated circuit substrate is between the first and second active regions, the first and  
seconds widths being less than a width of the transistor active region.

10

15